1. Record Nr. UNINA9910454563003321

Autore	Wardy Robert
Titolo	Aristotle in China : language, categories, and translation / / Robert Wardy [[electronic resource]]
Pubbl/distr/stampa	Cambridge : , : Cambridge University Press, , 2000
ISBN	1-107-11918-9 1-280-42121-5 0-511-48309-0 0-511-32747-1 0-511-17329-6 0-511-15235-3 0-521-77118-8 0-511-04944-7
Descrizione fisica	1 online resource (x, 170 pages) : digital, PDF file(s)
Collana	Needham Research Institute studies ; ; 2
Disciplina	181/.11
Soggetti	Philosophy, Chinese Chinese language Language and languages - Philosophy
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Title from publisher's bibliographic system (viewed on 05 Oct 2015).
Nota di bibliografia	Includes bibliographical references (p. 161-165) and index.
Nota di contenuto	The China syndrome: language, logical form, translation -- Guidance and constraint -- On the very idea of translation -- Whorf's hypothesis -- Deflationary philosophical anthropology -- Von Humboldt's legacy -- Case-study 1: conditionals -- Case-study 2: Chinese is a list -- Logical form -- Against 'logical' translation -- Why form might matter -- Procrustean logic -- Case-study 3: being -- Case-study 4: truth -- Case-study 5: nouns and ontology -- Aristotelian whispers -- What's in a name? -- Disputation, discrimination, inference -- The need for logic -- Finite and infinite -- The simple and the complex -- All the things there are -- How many questions? -- Relatively speaking -- Particular and general -- Translating the untranslatable.
Sommario/riassunto	In this book, Robert Wardy, a philosopher and classicist, turns his attention to the relation between language and thought. He explores

	this huge topic in an analysis of linguistic relativism, with specific reference to a reading of the ming li t'an ('The Investigation of the Theory of Names'), a seventeenth-century Chinese translation of Aristotle's Categories. Throughout his investigation, Wardy addresses important questions. Do the basis structures of language shape the major thought-patterns of its native speakers? Could philosophy be guided and constrained by the language in which it is done? What factors, from grammar and logic to cultural and religious expectations, influence translation? And does Aristotle survive rendition into Chinese intact? His answers will fascinate philosphers, Sinologists, classicists, linguists and anthropologists, and will make a major contribution to the existing literature.

2.

Record Nr.	UNINA9910144331103321
Autore	Kohler J. M (J. Michael), <1956->
Titolo	Etching in microsystem technology [[electronic resource] /] / Michael Kohler ; translated by Antje Wiegand
Pubbl/distr/stampa	Weinheim ; ; New York, : Wiley-VCH, c1999
ISBN	1-281-76426-4 9786611764265 3-527-61378-1 3-527-61379-X
Descrizione fisica	1 online resource (386 p.)
Disciplina	621.381531 660
Soggetti	Masks (Electronics) Microlithography Plasma etching Electronic books.
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references ([345]-360) and index.
Nota di contenuto	Etching in Microsystem Technology; Preface; Contents; Table of Contents; Symbols; Abbreviations; 1 Introduction; 2 Distinctive Features

of Microtechnical Etching; 2.1 Etching as a Fashioning Method; 2.1.1 Limits of Additive Microtechnical Pattern Generation; 2.1.2 Subtractive Pattern Generation; 2.2 Etch Rate and Selectivity; 2.2.1 Etch Rate and Time Request; 2.2.2 The Etching Process; 2.2.3 Transport Processes; 2.2.4 Process Velocities; 2.3. Isotropic and Anisotropic Etching; 2.4 Edge Geometry and Roughness; 2.4.1 Deviations from Ideal Geometry; 2.4.2 Flank Geometry in Isotropic Etching
2.4.3 Fabrication of Low Slope Angles by Isotropic Etching2.4.4 Flank Geometries in Anisotropic Etching; 2.4.5 Setting the Flank Geometry by Partial Anisotropic Etching; 2.5 Accuracy; 2.6 Monitoring of Etching Processes; 3 Wet-Chemical Etching Methods; 3.1 Etching at the Interface Solid-Liquid; 3.2 Preparation of the Surface; 3.2.1 Surface Condition; 3.2.2 Cleaning; 3.2.3 Digital Etching; 3.3 Etching of Dielectric Materials; 3.3.1 Wet Etching by Physical Dissolution; 3.3.2 Wet-Chemical Etching of Non-Metals; 3.4 Etching of Metals and Semiconductors; 3.4.1 Outer-Currentless Etching
3.4.2 Selectivity in Outer-Currentless Etching3.4.3 Etching of Multilayer Systems Forming Local Elements; 3.4.4 Geometry-Dependent Etch Rates; 3.4.5 Geometry-Dependent Passivation; 3.4.6 Electrochemical Etching; 3.4.7 Photochemical Wet Etching; 3.4.8 Photoelectrochemical Etching(PEC); 3.5 Crystallographic Etching; 3.5.1 Chemical Wet-Etching of Monocrystalline Surfaces; 3.5.2 Anisotropic Etching of Monocrystalline Metals; 3.5.3 Anisotropic Etching of Silicon; 3.5.4 Anisotropic Electrochemical and Photoelectrochemical Etching; 3.5.5 Porous Silicon
3 S.6 Anisotropic Etching of Compound Semiconductors3.6 Preparation of Free-Standing Micropatterns; 3.6.1 Surface Micromachining; 3.6.2 Bulk Micromachining; 3.6.3 Porous Silicon as Sacrificial Material; 4 Dry-Etching Methods; 4.1 Removal at the Interface Solid-Gas; 4.2 Plasma-Free Etching in the Gas Phase; 4.2.1 Plasma-Free Dry-Etching with Reactive Gases; 4.2.2 Photo-Assisted Dry Etching with Reactive Gases; 4.2.3 Directly Writing Micropatterning by Laser Scanning Etching; 4.2.4 Electron-Beam-Assisted Vapour Etching; 4.3 Plasma Etching Methods
4.3.1 Material Removal by Reactions with Plasma Species4.3.2 Plasma Generation; 4.3.3 Plasma Etching in the Barrel Reactor; 4.3.4 Plasma Etching in the Down-Stream Reactor; 4.3.5 Plasma Etching in the Planar-Plate Reactor; 4.3.6 Magnetic-Field-Enhanced Plasma Etching; 4.3.7 Plasma Etching at Low Pressure and High Ion Density; 4.3.8 Forming of Etch Structures in Plasma Etching; 4.3.9 Geometry Influence on Plasma Etching; 4.3.10 Plasma Jet Etching (PJE); 4.3.11 Applications of Plasma Etching; 4.4 Etchig Methods with Energized Particles; 4.4.1 Sputter-Etching; 4.4.2 Reactive Ion Etching (RIE)
4.4.3 Magnetic-Field-Enhanced Reactive Ion Etching (MERIE)

Sommario/riassunto

Microcomponents and microdevices are increasingly finding application in everyday life. The specific functions of all modern microdevices depend strongly on the selection and combination of the materials used in their construction, i.e., the chemical and physical solid-state properties of these materials, and their treatment. The precise patterning of various materials, which is normally performed by lithographic etching processes, is a prerequisite for the fabrication of microdevices.The microtechnical etching of functional patterns is a multidisciplinary area, the basis for the etching p